Desert Silicon
LIQUID SOURCE SOLUTIONS

Spin-on-Glass In-345

Elements of Interest	Key Element atoms/cm^3	Key Element % in Film
In, Si, O	In, 4E+21	In
Viscosity	**Thickness**	**Shelf Life**
0.9 cps	Coats 1500 Å at 3000 rpm Refractive Index = 1.50	20°C 3 months 4°C 9 months

Benefits

- Highest indium dopant profiles
- Uniform Coatings
- High purity materials
- Available with impurity specification of less than 1 ppm or less than 50 ppb.
- Lower maintenance and cost of ownership
- Stable processing independent of flow rates

Custom target concentration levels available

Typical Application

The concentration of the source for driving-in is typically high; in the range of 4E+21 leaves a high concentration of dopant right at the surface. During drive in the dopant diffuses into the substrate. In-345 adds a level of dopant consistent with the final desired concentration. It begins curing at about 200°C to give a less dense but solid film. It continues to become increasingly dense as bakes continue to 350°C or higher. We recommend baking at the highest temperature the material will see in any post processing. For doping applications the glass is often removed after drive in.

Available in

- 240ml
- 500ml
- 1 Liter
- 2.5 L
- 4 Liter

Alternative Products

Other target concentration levels available

Alternate Elements to Add

- As
- Sb
- Ga
- Al
- Sn

Other elements available for compound semiconductor use

Spin-on-Glass In-345